



# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

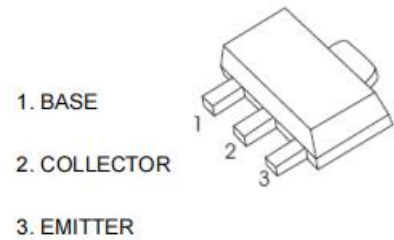
2SB804

## SOT-89 Bipolar Transistor 双极型三极管

### ■ Features 特点

PNP General Purpose 通用

### ■ Absolute Maximum Ratings 最大额定值



| Characteristic 特性参数                         | Symbol 符号              | Rat 额定值               | Unit 单位       |
|---------------------------------------------|------------------------|-----------------------|---------------|
| Collector-Base Voltage 集电极基极电压              | $V_{CBO}$              | -100                  | V             |
| Collector-Emitter Voltage 集电极发射极电压          | $V_{CEO}$              | -80                   | V             |
| Emitter-Base Voltage 发射极基极电压                | $V_{EBO}$              | -5                    | V             |
| Collector Current 集电极电流                     | $I_C$                  | -1000                 | mA            |
| Power dissipation 耗散功率                      | $P_C(T_a=25^{\circ}C)$ | 500                   | mW            |
| Thermal Resistance Junction-Ambient 热阻      | $R_{\theta JA}$        | 250                   | $^{\circ}C/W$ |
| Junction and Storage Temperature<br>结温和储藏温度 | $T_J, T_{stg}$         | -55to+150 $^{\circ}C$ |               |

### ■ Device Marking 产品打标

|          |           |            |            |
|----------|-----------|------------|------------|
| $H_{FE}$ | 90-180(W) | 135-270(V) | 200-400(U) |
| Mark     | AW        | AV         | AU         |

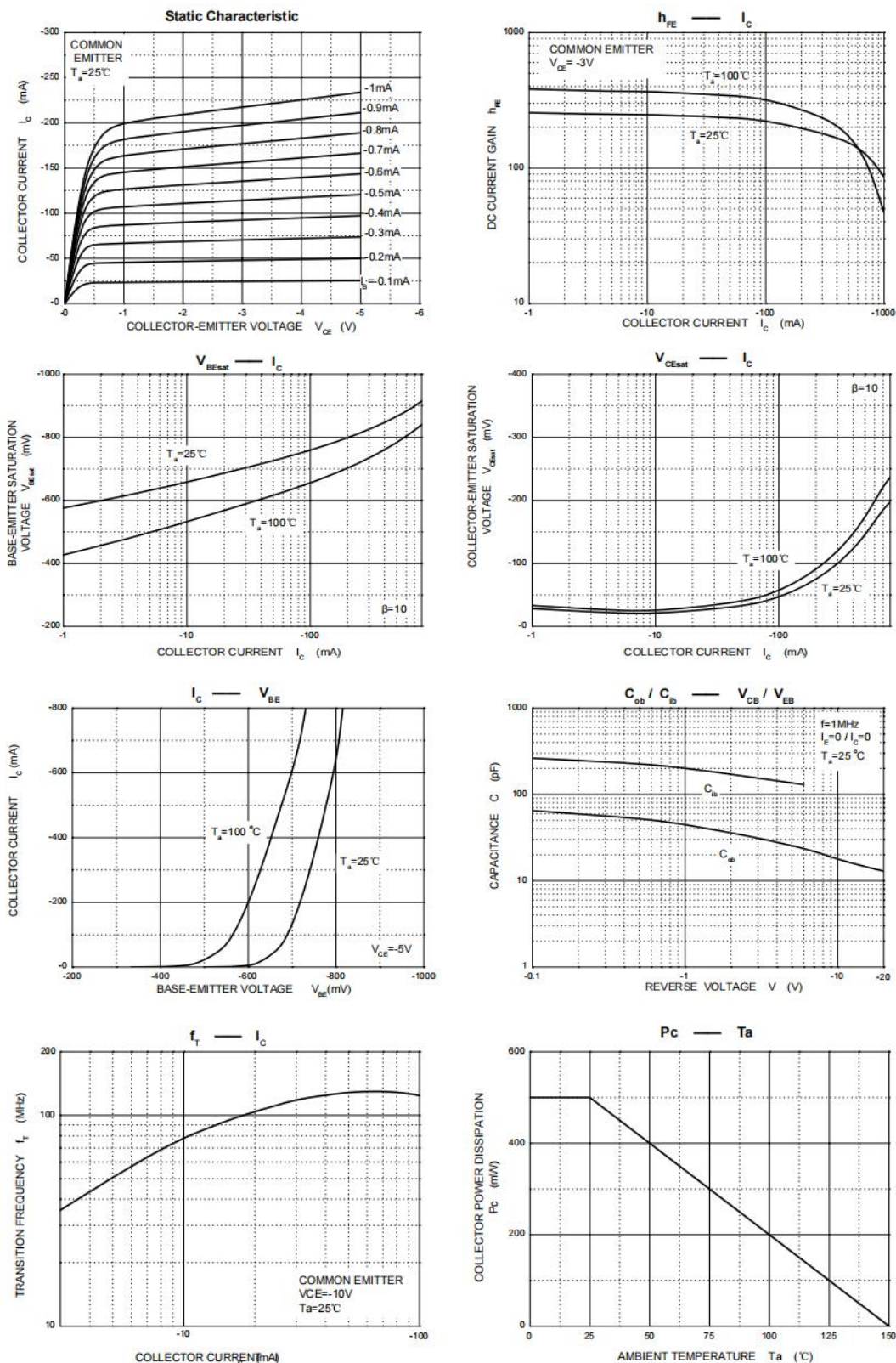


## ■Electrical Characteristics 电特性

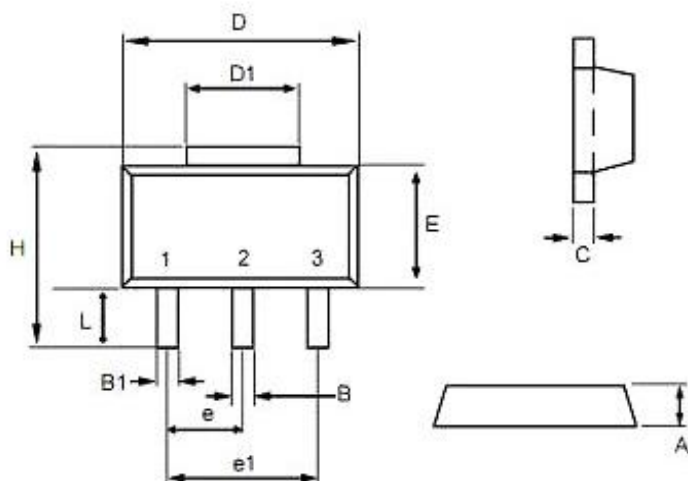
(TA=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

| Characteristic<br>特性参数                                                                                                    | Symbol<br>符号         | Min<br>最小值 | Type<br>典型值 | Max<br>最大值 | Unit<br>单位 |
|---------------------------------------------------------------------------------------------------------------------------|----------------------|------------|-------------|------------|------------|
| Collector-Base Breakdown Voltage<br>集电极基极击穿电压(I <sub>C</sub> = -50μA, I <sub>E</sub> =0)                                  | BV <sub>CBO</sub>    | -100       | —           | —          | V          |
| Collector-Emitter Breakdown Voltage<br>集电极发射极击穿电压(I <sub>C</sub> = -2mA, I <sub>B</sub> =0)                               | BV <sub>CEO</sub>    | -80        | —           | —          | V          |
| Emitter-Base Breakdown Voltage<br>发射极基极击穿电压(I <sub>E</sub> = -50μA, I <sub>C</sub> =0)                                    | BV <sub>EBO</sub>    | -5         | —           | —          | V          |
| Collector-Base Leakage Current<br>集电极基极漏电流(V <sub>CB</sub> = -100V, I <sub>E</sub> =0)                                    | I <sub>CBO</sub>     | —          | —           | -0.1       | μA         |
| Emitter-Base Leakage Current<br>发射极基极漏电流(V <sub>EB</sub> = -5V, I <sub>C</sub> =0)                                        | I <sub>EBO</sub>     | —          | —           | -0.1       | μA         |
| DC Current Gain(V <sub>CE</sub> = -2V, I <sub>C</sub> = -100mA)<br>直流电流增益(V <sub>CE</sub> = -2V, I <sub>C</sub> = -500mA) | H <sub>FE</sub>      | 90<br>25   | —           | 400        |            |
| Collector-Emitter Saturation Voltage<br>集电极发射极饱和压降(I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA)                       | V <sub>CE(sat)</sub> | —          | —           | -0.5       | V          |
| Base-Emitter Saturation Voltage<br>基极发射极饱和压降(I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA)                             | V <sub>BE(sat)</sub> | —          | —           | -1.5       | V          |
| Base-Emitter On Voltage<br>基极发射极导通电压(V <sub>CE</sub> = -10V, I <sub>C</sub> = -500mA)                                     | V <sub>BE(on)</sub>  | —          | —           | -1.5       | V          |
| Transition Frequency<br>特征频率(V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA)                                               | f <sub>T</sub>       | —          | 80          | —          | MHz        |
| Output Capacitance<br>输出电容(V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f=1MHz)                                             | C <sub>ob</sub>      | —          | 26          | —          | pF         |

## ■ Typical Characteristic Curve 典型特性曲线



## ■Dimension 外形封装尺寸



| Dim | min      | max  |
|-----|----------|------|
| A   | 1.40     | 1.60 |
| B   | 0.40     | 0.56 |
| B1  | 0.35     | 0.48 |
| C   | 0.35     | 0.44 |
| D   | 4.40     | 4.60 |
| D1  | 1.35     | 1.83 |
| e   | 1.50 BSC |      |
| e1  | 3.00 BSC |      |
| E   | 2.29     | 2.60 |
| H   | 3.75     | 4.25 |
| L   | 0.80     | 1.20 |